AMENDMENTS TO THE CLAIMS:

Claims 1-16 (canceled)

17. (Currently Amended) A semiconductor device[,] comprising:

a silicon semiconductor substrate;

a gate insulating film and a gate electrode formed on a main surface of said semiconductor substrate;

a conductive film containing germanium or a conductive film made of silicon carbide, said conductive film being formed on a silicon-exposed region on the main surface of the semiconductor substrate;

a silicon film formed on said conductive film on said region; and

source/drain [regions] layers formed in those regions of the silicon semiconductor substrate region, which are below said silicon film and said conductive film;

wherein said silicon film is a polycrystalline film or a monocrystalline film having a dislocation density of at least $10^8 cm^{-2}$.

18. (Currently Amended) The semiconductor device according to claim 17, wherein said silicon film [deposited] formed on said conductive film is a polycrystalline film or a monocrystalline film having a dislocation density of at least $10^8 cm^{-2}$.

19. (Original) The semiconductor device according to claim 17, wherein said conductive film containing germanium contains at least 20 atomic % of germanium.

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20. (Original) The semiconductor device according to claim 17, wherein said conductive film containing germanium contains at least 1 x $10^{16}cm^{-2}$ of germanium in terms of areal density.

21. (Original) The semiconductor device according to claim 17, wherein said silicon carbide film has a film thickness of 0.1 to 10 nm.

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